

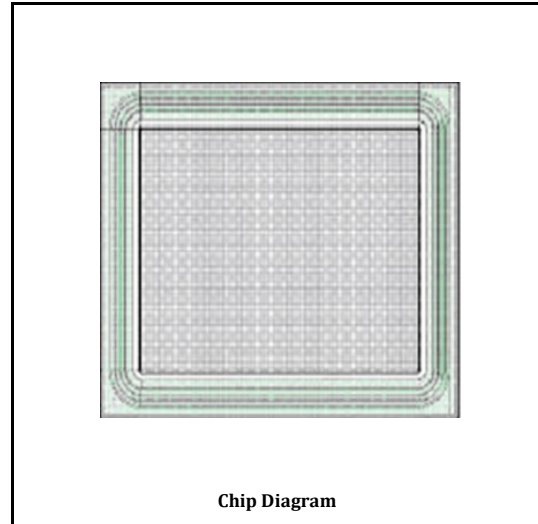
PRODUCT FEATURES

- ◆ Ultrafast Recovery Time
- ◆ Soft Recovery Characteristics
- ◆ Low Forward Voltage
- ◆ Low Leakage Current
- ◆ Low Recovery Loss

Applications (not limited to)

- ◆ Freewheeling, Snubber, Clamp
- ◆ Snubber Diode
- ◆ Switch Power Supplies
- ◆ Motor control
- ◆ Inverters, Converters

Items	Description
Wafer Size	5 Inch
Gross Die	270 EA
Top Metal	Al/Ag
Back Metal	Ag
Dimensions	um
Chip Size	5100um * 7500um
Pad Size	4050um * 6050um
Wafer Thickness	260±20um
Scribe Line width	50 um
Bonding Wire In case top metal=Al	Al, 18mil*3



Absolute Maximum ratings (T_a=25℃)

Parameter	Symbol	Value	Units
DC Blocking Voltage	V _{RRM}	1200	V
Average Rectified Forward Current	I _{FAV}	60	A
Nonrepetitive Peak Surge Current@8.3mS	I _{FSM}	500	A
Operating Junction Temperature	T _j	175	℃
Storage Temperature	T _{STG}	- 55~175	℃

Electrical specification (T_a=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Breakdown Voltage	V _{BR}	I _R =100μA	1200	1350	-	V
Forward Voltage	V _F	I _F =60A, T _a =25℃	-	2.80	3.30	V
		I _F =60A, T _a =125℃	-	2.10	2.80	V
Reverse Leakage Current	I _R	V _R =1200V, T _a =25℃	-	-	10	μA
		V _R =1200V, T _a =125℃	-	-	500	μA
Reverse Recovery Time	T _{rr}	I _F =0.5A, I _R =1A, I _{rr} =0.25A	-	65	85	ns
		I _F =1A, V _R =30V, di/dt=-200A/us	-	36	-	ns

Remark:

- 1.Customer should obtain the latest version of datasheet before placing order, and verify the relevant information.
- 2.Cutting damage and chipping area can't beyond scribe line in given size range.
- 3.Testing system of T_{rr} could be different, customer might take secondary test to evaluate if necessary.
- 4.Customer might choose the bonding wire material and diameter according to actual situation, while no less than our recommendation.